



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	I <sub>D</sub> T <sub>C</sub> = +25°C		
650V	$1.4\Omega$ @ $V_{GS} = 10V$	5.5A		

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

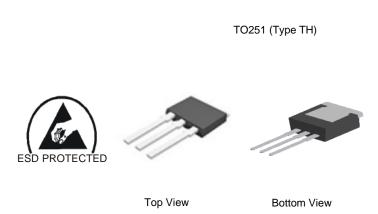
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

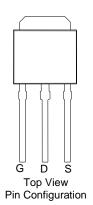
# **Features and Benefits**

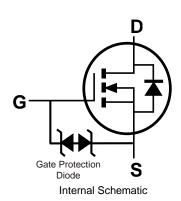
- Low On-Resistance
- High BV<sub>DSS</sub> Rating for Power Application
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 63
- Weight: 0.33 grams (Approximate)







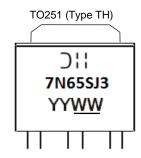
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMG7N65SJ3	TO251 (Type TH)	75 Pieces / Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



☐ I I = Manufacturer's Marking
7N65SJ3= Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	650	V
Gate-Source Voltage		Vgss	±30	V
Continuous Drain Current (Note 5) Vgs = 10V	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	lo	5.5 3.7	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C	I <sub>D</sub>	0.7	А
Maximum Body Diode Forward Current (Note 5)		Is	5.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	10	A
Avalanche Current (Note 6)	L = 60mH	las	1.7	A
Avalanche Energy (Note 6)	L = 60mH	Eas	87	mJ
Peak Diode Recovery dv/dt (Note 6)		dv/dt	3	V/ns

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>C</sub> = +25°C	D-	125	W
Total Fower Dissipation (Note 3)	T <sub>C</sub> = +100°C	PD	50	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	70	°C/W
Thermal Resistance, Junction to Case (Note 5)		Rejc	1	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	650	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μA	V <sub>DS</sub> = 650V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	10	μA	$V_{GS} = \pm 24V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	3	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	1.1	1.4	Ω	Vgs = 10V, ID = 2.5A	
Diode Forward Voltage	VsD	_	0.84	1.5	V	Vgs = 0V, Is = 5A	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss		886			V <sub>DS</sub> = 50V, f = 1MHz, V <sub>GS</sub> = 0V	
Output Capacitance	Coss		62		pF		
Reverse Transfer Capacitance	Crss		8.8				
Gate Resistance	Rg	_	1.36	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	25	_		V <sub>DS</sub> = 480V, I <sub>D</sub> = 5A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Qgs	_	3.5	_	nC		
Gate-Drain Charge	Qgd	_	12.4	_		VGS = 10V	
Turn-On Delay Time	td(on)	_	10	_		V <sub>DS</sub> = 300V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 4.7Ω, I <sub>D</sub> = 2.5A	
Turn-On Rise Time	t <sub>R</sub>	_	11	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	36	_	115		
Turn-Off Fall Time	tF		15				
Body Diode Reverse Recovery Time	t <sub>RR</sub>		245		ns	V <sub>DS</sub> =100V, I <sub>F</sub> = 5A,	
Body Diode Reverse Recovery Charge	Qrr		1.89		μC	dl/dt = 100A/µs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

Guaranteed by design. Not subject to production testing.
 Short duration pulse test used to minimize self-heating effect.



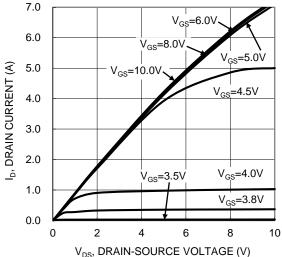


Figure 1. Typical Output Characteristic

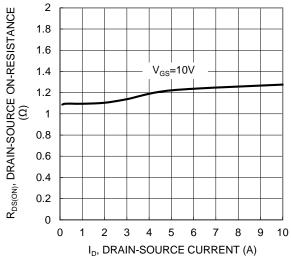


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

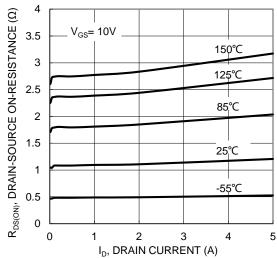


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

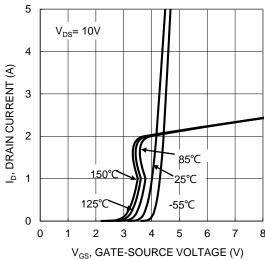


Figure 2. Typical Transfer Characteristic

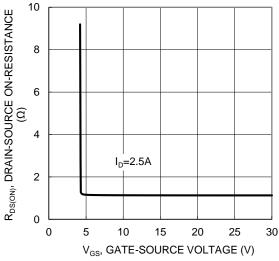


Figure 4. Typical Transfer Characteristic

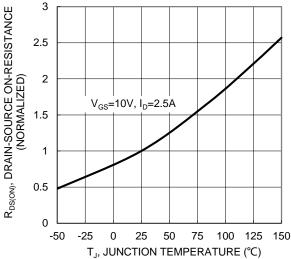


Figure 6. On-Resistance Variation with Junction Temperature



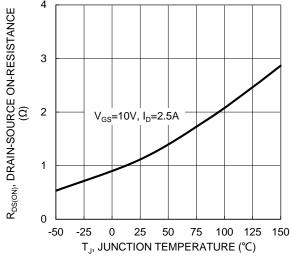
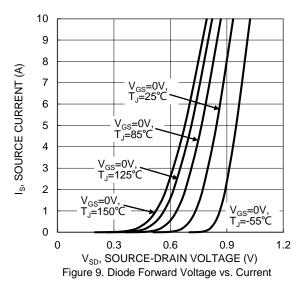


Figure 7. On-Resistance Variation with Junction Temperature



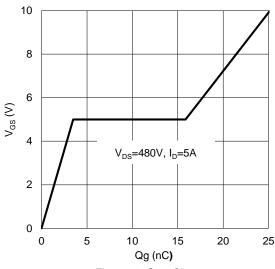


Figure 11. Gate Charge

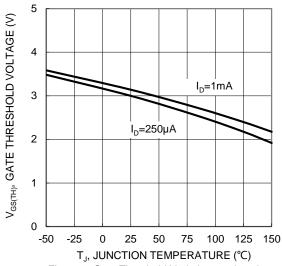
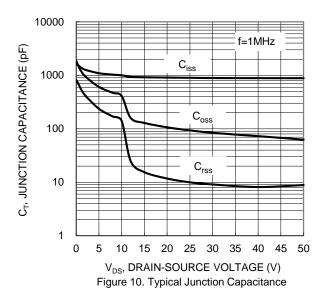


Figure 8. Gate Threshold Variation vs. Junction Temperature



100 \_\_\_\_  $R_{DS(ON)}$  LIMITED 10 ID, DRAIN CURRENT (A) :100µs 1 T<sub>J(MAX)</sub>=150°C 0.1 Single Pulse DUT on infinite heatsink  $V_{GS}=10V$ 0.01 100 1000 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



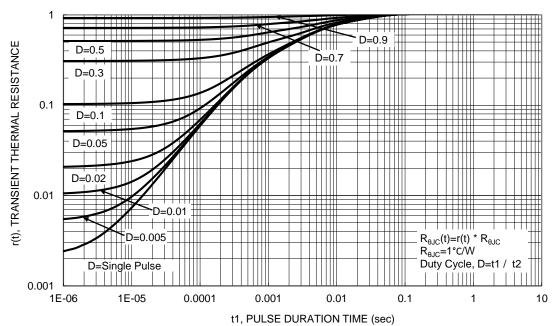


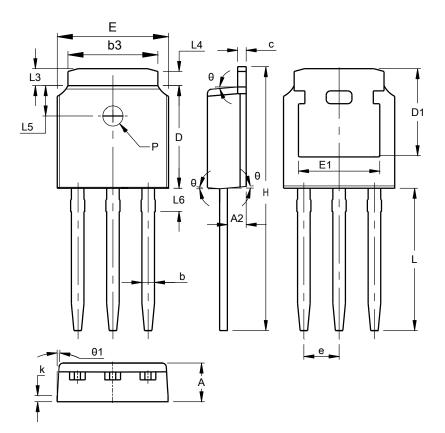
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

### TO251 (Type TH)



TO251 (Type TH)					
Dim	Min	Тур			
Α	2.20	2.40	2.30		
A2	0.97	1.17	1.07		
b	0.68	0.90	0.78		
b3	5.20	5.50	5.33		
С	0.43	0.63	0.53		
D	5.98	6.22	6.10		
D1	5	.30 RE	F		
е	2.	286 BS	C		
Е	6.40	6.80	6.60		
E1	4.63	5.03	4.83		
H	16.22	16.82	16.52		
k	0.40REF				
L	9.15	9.65	9.40		
L3	0.88	1.28	1.02		
L4	0.75 REF				
L5	1.65	1.95	1.80		
L6	0.85	1.25	1.05		
PØ	1.20				
θ	5°	9°	7°		
θ1	5°	9°	7°		
All Dimensions in mm					



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